NSN 5961-01-413-4336

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-413-4336 **Inclosure Material:** Metal or glass **Overall Length:** 0.560 inches **Overall Height:** 0.255 inches **Overall Width:** 0.370 inches **Function For Which Designed:** Bidirectional **Component Name And Quantity:** 4 semiconductor device diode **Mounting Method: Terminal Semiconductor Material:** Silicon all semiconductor Voltage Rating In Volts Per Characteristic: 2.15 forward voltage, peak all semiconductor device diode **Current Rating Per Characteristic:** 4.00 amperes forward current, average blank all semiconductor device diode and 90.00 amperes peak forward surge current nanoamperes all semiconductor device diode and 300.00 amperes source cutoff current universal all semiconductor device diode **Power Rating Per Characteristic:** 2.5 watts small-signal input power, common-collector preset all semiconductor device diode **Capacitance Rating In Picofarads:** 95.0 all semiconductor **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** Varistor diode assembly **Test Data Document:** 49956-g204968 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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Yes - demil/mli